

RELIABILITY REPORT

FOR

MAX216CWN+

PLASTIC ENCAPSULATED DEVICES

September 10, 2010

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR. SUNNYVALE, CA 94086

Approved by				
Don Lipps				
Quality Assurance				
Manager, Reliability Engineering				



# Conclusion

The MAX216CWN+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim"s continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim"s quality and reliability standards.

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# I. Device Description

A. General

The MAX216 Transceiver is deisnged specifically for communicating with AppleTalk™ interfaces. The MAX216 has one differential and one single-ended driver, plus one differential and two single-ended receivers, all of which meet the AppleTalk transceiver specifications. (See data sheet for more details)



#### II. Manufacturing Information

A. Description/Function: Low-Power, AppleTalk™ Interface Transceiver

B. Process: S3

C. Number of Device Transistors:

D. Fabrication Location: Oregon

E. Assembly Location: Malaysia, Philippines

F. Date of Initial Production: Pre 1997

# III. Packaging Information

A. Package Type: 18-pin SOIC (W)

B. Lead Frame: Copper

C. Lead Finish:

D. Die Attach:

Conductive

E. Bondwire:

Au (1.3 mil dia.)

F. Mold Material:

G. Assembly Diagram:

#05-1901-0024

H. Flammability Rating:

Class UL94-V0

I. Classification of Moisture Sensitivity per Level 1

JEDEC standard J-STD-020-C

J. Single Layer Theta Ja: 105°C/W
K. Single Layer Theta Jc: 22°C/W
L. Multi Layer Theta Ja: N/A
M. Multi Layer Theta Jc: N/A

## IV. Die Information

A. Dimensions: 88 X 113 mils

B. Passivation: Si<sub>3</sub>N<sub>4</sub>/SiO<sub>2</sub> (Silicon nitride/ Silicon dioxide)

C. Interconnect: Al/0.5%Cu with Ti/TiN Barrier

D. Backside Metallization: None

E. Minimum Metal Width: 3.0 microns (as drawn)F. Minimum Metal Spacing: 3.0 microns (as drawn)

G. Bondpad Dimensions: 5 mil. Sq.
H. Isolation Dielectric: SiO<sub>2</sub>
I. Die Separation Method: Wafer Saw



#### V. Quality Assurance Information

A. Quality Assurance Contacts: Don Lipps (Manager, Reliability Engineering)

Bryan Preeshl (Managing Director of QA)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm</li>D. Sampling Plan: Mil-Std-105D

## VI. Reliability Evaluation

#### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( \( \lambda \)) is calculated as follows:

$$\chi = \frac{1}{MTTF}$$
 =  $\frac{1.83}{192 \times 4340 \times 79 \times 2}$  (Chi square value for MTTF upper limit)

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$x = 13.9 \times 10^{-9}$$

% = 13.9 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim"s reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maxim-ic.com/qa/reliability/monitor. Cumulative monitor data for the S3 Process results in a FIT Rate of 0.04 @ 25C and 0.69 @ 55C (0.8 eV, 60% UCL)

#### B. E.S.D. and Latch-Up Testing (lot XKRAEY007AQ, D/C 9335)

The RS09 die type has been found to have all pins able to withstand a HBM transient pulse of +/-600V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-50mA.



# **Table 1**Reliability Evaluation Test Results

# MAX216CWN+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (No	ote 1)  Ta = 135°C  Biased  Time = 192 hrs.	DC Parameters & functionality	79	0	XKRAEY007AQ, D/C 9335

Note 1: Life Test Data may represent plastic DIP qualification lots.